

ABSTRACT

The present invention relates to a Schottky barrier diode which contains a substrate region of a first conductivity type formed in a semiconductor material layer of same conductivity type and a metal layer. A doped region of a second conductive type is formed in the semiconductor layer, with the doped region disposed under the material layer and separated from other doped regions by portions of the semiconductor layer.

10053365-014332
200310-0906001